Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	(("4","754","310") or ("5","216",	US-PGPUB;	OR	OFF	2004/03/12 11:48
		"275")).PN.	USPAT; USOCR			
00	40	(///4400705!)\ == (4700400!)\ ==		00	OFF	2004/02/42 44.40
S2	10	(("4409725") or ("4763180") or ("4878096") or ("4879255") or	US-PGPUB; USPAT;	OR	OFF	2004/03/12 11:49
1		("5523966") or ("4261761") or	USOCR	,		
		("4402761") or ("4621412") or ("4825420") or ("4969020")).PN.				
60	40		LIC DODLIB	OB	OFF	2004/03/12 11:54
S3	40	(("5198687") or ("5202750") or ("5293054") or ("5294816") or	US-PGPUB; USPAT;	OR	OF I	2004/03/12 11:54
		("5296725") or ("5306930") or	USOCR			
		("5315150") or ("5336911") or ("5444272") or ("5489787") or				
		("5510623") or ("5623151") or				
		("5663079") or ("5719411") or				
		("5757034") or ("5793066") or ("4281544") or ("4288806") or				
		("4349743") or ("4384217") or				
		("4388541") or ("4414560") or				
		("4420379") or ("4494304") or ("4505759") or ("4538117") or				
		('4547791") or ('4575642") or				
		("4580154") or ("4631748") or				
		("4783694") or ("4786830") or ("4866315") or ("4887142") or				
		("4921811") or ("4941030") or				
		("4950616") or ("4954731") or				
0.4	0.4	("4959703") or ("4965872")) PN	HE DODUB	OR	OFF	2004/03/12 13:08
S4	64	superjunction	US-PGPUB; USPAT	OK	OFF	
S5	185	fujihira:in:	US-PGPUB;	OR	OFF	2004/03/12 12:04
			USPAT			0004/00/40 40 40
S6	117	S5 and semiconductor	US-PGPUB; USPAT	OR	OFF	2004/03/12 12:12
S7	1309	257/330	US-PGPUB;	OR	OFF	2004/03/12 12:12
			USPAT		055	0004/00/40 40:40
S8	14	S7 and S4	US-PGPUB; USPAT	OR	OFF	2004/03/12 12:12
S9	11	("20020105026" "4626879"	US-PGPUB;	OR	OFF	2004/03/12 12:55
		"4754310" "4963947" "5168328" "5216275" "5264719"	USPAT; USOCR			
		3210273 3204713 "5294824" "5438215" "6097063"	USCCIT			
) "6184555"):PN				
S10	27	superjunction	USOCR;	OR	OFF	2004/03/12 13:46
			EPO; JPO; DERWENT;			
			IBM_TDB			
S11	3	jp-07086580-\$:did.:or	USOCR;	OR	OFF	2004/03/12 13:47
		jp-07245410-\$ did. or	EPO; JPO;			
		ep-0053854-\$.did. or ep-0164096-\$.did.	DERWENT;			

S12	24	("3171068" "33 "3413527" "34	370209" 17301" "3515952"	US-PGPUB; USPAT;	OR	OFF	2004/03/12 13:48
		"3660732" "3	925803"	USOCR			
		"4109270" "41 "4134123" "4	17508" "4132904" 160261"				
		"4163237" "41	63241" ["] 4219835"				
		"4296429" "4 "4379305" "44	•				
S13	70	("4754310").UR	PN:	USPAT	OR	OFF	2004/03/12 13:51

No.	Publication No.	Title
1.	2003 - 264286	METHOD FOR MANUFACTURING SUPERJUNCTION SEMICONDUCTOR ELEMENT
2.	2003 - 229569	MANUFACTURING METHOD FOR SUPERJUNCTION SEMICONDUCTOR ELEMENT
3.	2003 - 115588	LATERAL SUPERJUNCTION SEMICONDUCTOR DEVICE
4.	2003 - 101037	SEMICONDUCTOR ELEMENT
5.	<u> 2003 - 101022</u>	POWER SEMICONDUCTOR DEVICE
6.	2003 - 069040	SILICON CARBIDE SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF
7.	2002 - 217415	HIGH-VOLTAGE PERPENDICULAR CONDUCTIVE SUPERJUNCTION SEMICONDUCTOR DEVICE
8.	2002 - 203963	METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE
9.	<u> 2002 - 134748</u>	SUPERJUNCTION SEMICONDUCTOR DEVICE
10.	2002 - 110693	DIAGONAL INJECTION METHOD FOR EXECUTION OF DOPING TO SIDEWALL OF DEEP POROUS TRENCH
11.	<u> 2001 - 313391</u>	SEMICONDUCTOR DEVICE
12.	2001 - 015752	SUPERJUNCTION SEMICONDUCTOR ELEMENT AND MANUFACTURE THEREOF
13.	<u> 2000 – 277726</u>	HIGH BREAKDOWN STRENGTH SEMICONDUCTOR ELEMENT
14.	2000 - 156978	SOFT SWITCHING CIRCUIT
15.	2000 - 040822	SUPERJUNCTION SEMICONDUCTOR ELEMENT AND ITS MANUFACTURE

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Most Frequently Occurring Classifications of Patents Returned From A Search of 10/649,929 on March 09, 2004

Combined Classifications

10 257/E29.214
10 257/E29.216
7 257/133
5 257/137
5 257/370
5 257/378
4 257/132
4 257/138
4 257/146
4 257/163
4 257/401
4 257/E21.696
4 257/E27.031
4 257/E29.048
4 257/E29.198
3 257/152
3 257/335
3 257/338
3 257/E27.015
3 257/E27.064
3 257/E29.257
3 438/207
2 257/139
2 257/144
2 257/154
2 257/155

2 257/273 2 257/332 2 257/341 2 257/342 2 257/371 2 257/382 2 257/402 2 257/409 2 257/768 2 257/E21.417 2 257/E21.538 2 257/E21.544 2 257/E21.632 2 257/E29.037 2 257/E29.067 2 257/E29.194 2 257/E29.212 2 257/E29.219 2 257/E29.256 2 327/434 2 327/566 2 365/204 2 438/226 2 438/271 2 438/450 2 438/586

Titles of Most Frequently Occurring Classifications of Patents Returned From A Search of 10/649.929 on March 09, 2004

(3 OR, 4 XR) 7 257/133 Class 257: ACTIVE SOLID-STATE DEVICES ..Triggered by V BO overvoltage means 257/111 257/133 .Combined with field effect transistor 5 257/137 (3 OR, 2 XR) Class 257: ACTIVE SOLID-STATE DEVICES 257/111 ..Triggered by V BO overvoltage means .Combined with field effect transistor 257/133 ..Having controllable emitter shunt 257/137 5 257/370 (1 OR, 4 XR) Class 257: ACTIVE SOLID-STATE DEVICES 257/264 ...Enhancement mode or with high resistivity channel (e.g., doping of 10 15 cm -3 or less) .Having insulated electrode (e.g., MOSFET, MOS 257/288 diode) .. Insulated gate field effect transistor in 257/368 integrated circuit ...Complementary insulated gate field effect 257/369 transistorsCombined with bipolar transistor 257/370 5 257/378 (1 OR, 4 XR) Class 257: ACTIVE SOLID-STATE DEVICES 257/264 ... Enhancement mode or with high resistivity channel (e.g., doping of 10 15 cm -3 or less) .Having insulated electrode (e.g., MOSFET, MOS 257/288 diode) .. Insulated gate field effect transistor in 257/368 integrated circuit ... Combined with bipolar transistor 257/378 4 257/132 (1 OR, 3 XR) Class 257: ACTIVE SOLID-STATE DEVICES ..Triggered by V BO overvoltage means 257/111 .Five or more layer unidirectional structure 257/132 4 257/138 (1 OR, 3 XR) Class 257: ACTIVE SOLID-STATE DEVICES ..Triggered by V BO overvoltage means 257/111 .Combined with field effect transistor 257/133 ..Having controllable emitter shunt 257/137 ...Having gate turn off (GTO) feature 257/138 (0 OR, 4 XR) 4 257/146 Class 257: ACTIVE SOLID-STATE DEVICES 257/111 ..Triggered by V BO overvoltage means .Combined with other solid-state active device 257/146 in integrated structure 4 257/163 (1 OR, 3 XR)

Class 257: ACTIVE SOLID-STATE DEVICES

PLUS Search Results for S/N 10/649,929, Searched March 09, 2004 (Top 50)

The Patent Linguistics Utility System (PLUS) is a USPTO automated search system for U.S. Patents from 1971 to the present. PLUS is a query-by-example search system which produces a list of patents that are most closely related linguistically to the application searched. This search was prepared by the staff of the Scientific and Technical Information Center, SIRA.

4409725	5198687	5510623	4388541	4783694
4763180	5202750	5623151	4414560	4786830
4878096	5293054	5663079	4420379	4866315
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4402761	5315150	4281544	4547791	4950616
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4825420	5444272	4349743	4580154	4959703
4969020	5489787	4384217	4631748	4965872